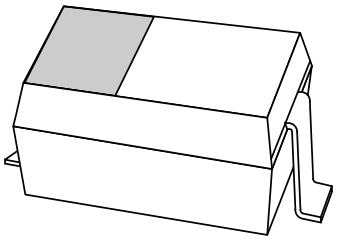
DATA SHEET



1PS76SB10
Schottky barrier diode

Product specification

1996 Oct 14

Philips
Semiconductors

PHILIPS

Schottky barrier diode 1PS76SB10

FEATURES

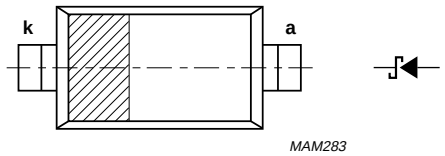
- Low forward voltage
- Guard ring protected
- Very small plastic SMD package.

APPLICATIONS

- Ultra high-speed switching
- Voltage clamping
- Protection circuits
- Blocking diodes.

DESCRIPTION

Planar Schottky barrier diode encapsulated in a SOD323 very small plastic SMD package.



Marking code: S0.
The marking bar indicates the cathode.

Fig.1 Simplified outline (SOD323) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_R	continuous reverse voltage		–	30	V
I_F	continuous forward current		–	200	mA
I_{FRM}	repetitive peak forward current	$t_p \leq 1$ s; $\delta \leq 0.5$	–	300	mA
I_{FSM}	non-repetitive peak forward current	$t_p < 10$ ms	–	600	mA
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	125	°C
T_{amb}	operating ambient temperature		–65	+125	°C

ELECTRICAL CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V_F	forward voltage	see Fig.2		
		I_F = 0.1 mA	240	mV
		I_F = 1 mA	320	mV
		I_F = 10 mA	400	mV
		I_F = 30 mA	500	mV
		I_F = 100 mA	800	mV
I_R	reverse current	V_R = 25 V; note 1; see Fig.3	2	µA
C_d	diode capacitance	f = 1 MHz; V_R = 1 V; see Fig.4	10	pF

Note

1. Pulsed test: t_p = 300 µs; δ = 0.02.

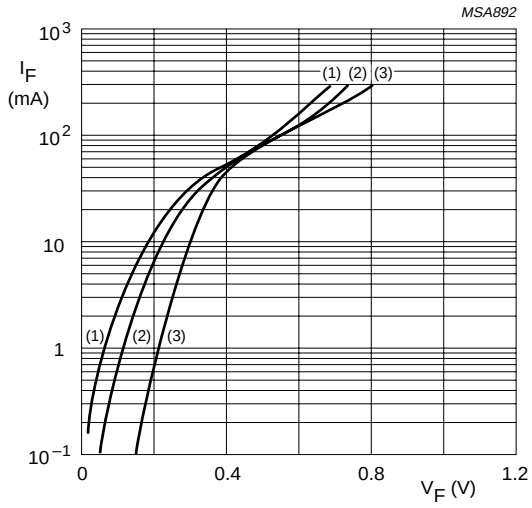
THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	note 1	450	K/W

Note

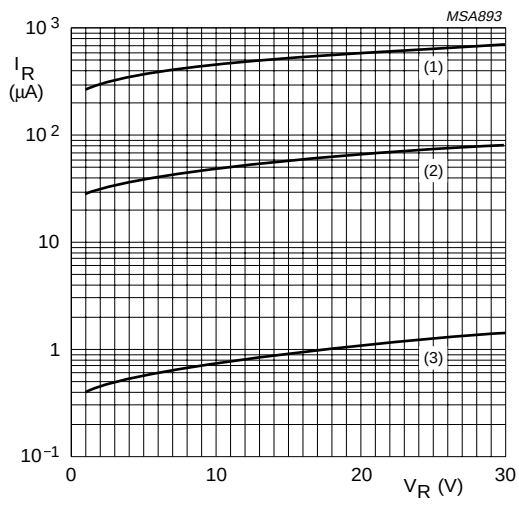
1. Refer to SOD323 standard mounting conditions.

GRAPHICAL DATA



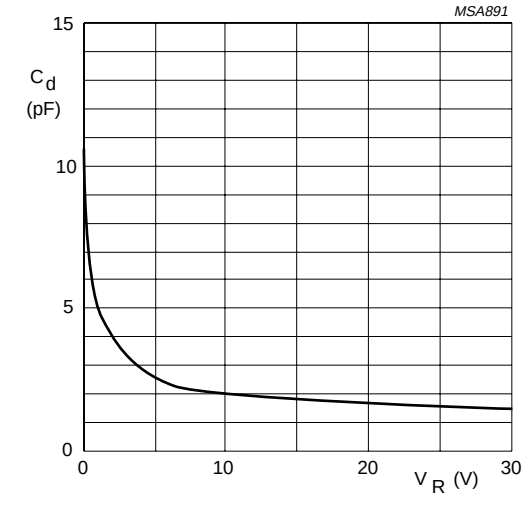
(1) T_{amb} = 125 °C.
(2) T_{amb} = 85 °C.
(3) T_{amb} = 25 °C.

Fig.2 Forward current as a function of forward voltage; typical values.



(1) T_{amb} = 125 °C.
(2) T_{amb} = 85 °C.
(3) T_{amb} = 25 °C.

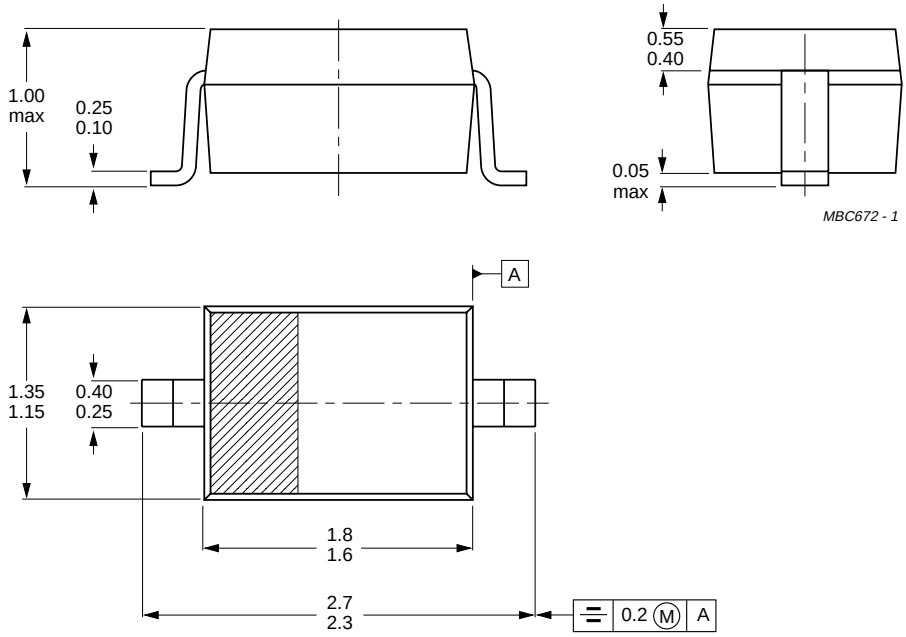
Fig.3 Reverse current as a function of reverse voltage; typical values.



f = 1 MHz; T_{amb} = 25 °C.

Fig.4 Diode capacitance as a function of reverse voltage; typical values.

PACKAGE OUTLINE



Dimensions in mm.

The marking bar indicates the cathode.

Fig.5 SOD323.

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.